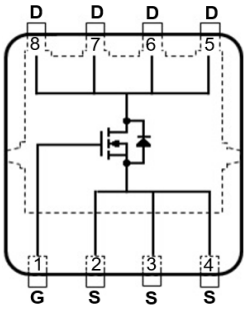
PJQ65702U3-AU

100V N-Channel MOSFET, U3 series with Enhanced SOA

Voltage 100 V **Current** 340 A

PDFN8080-8L





Features

- Optimized for hot-swap and e-fuse applications
- Enhanced Safe Operation Area (SOA) for robust linear mode operation
- $R_{DS(ON)}$, V_{GS}@10V, I_D@50A<1.65mΩ
- Standard Level Drive
- 100% UIS tested
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : PDFN8080-8L Package
- Approx. Weight : 0.2 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current(Note 3)	T_C=25°C	I_D	340	A
	T_C=100°C		240	
Pulsed Drain Current(Note 1)	T_C=25°C	I_{DM}	1360	
Power Dissipation	T_C=25°C	P_D	395	W
	T_C=100°C		197	
Continuous Drain Current(Note 4)	T_A=25°C	I_D	38	A
	T_A=70°C		32	
Power Dissipation	T_A=25°C	P_D	4.7	W
	T_A=70°C		3.3	
Single Pulse Avalanche Current(Note 5)		I_{AS}	45	A
Single Pulse Avalanche Energy(Note 5)		E_{AS}	1013	mJ
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~175	°C
Thermal Resistance(Note 4)	Junction to Case	$R_{\theta JC}$	0.38	°C/W
	Junction to Ambient	$R_{\theta JA}$	32	

PJQ65702U3-AU

Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=1mA	2	2.7	3.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=50A	-	1.3	1.65	mΩ
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Dynamic(Note 6)						
Total Gate Charge	Q_g	V_{DS}=50V, I_D=50A, V_{GS}=10V	-	239	310	nC
Gate-Source Charge	Q_{gs}		-	57	-	
Gate-Drain Charge	Q_{gd}		-	34	-	
Input Capacitance	Ciss	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	16934	22000	pF
Output Capacitance	Coss		-	3778	5000	
Reverse Transfer Capacitance	Crss		-	90	180	
Gate resistance	R_g	f=1MHz	-	0.85	-	Ω
Turn-On Delay Time	$td_{(on)}$	V_{DS}=50V, I_D=50A, V_{GS}=10V, R_G=3Ω (Note 2)	-	52	-	ns
Turn-On Rise Time	t_r		-	56	-	
Turn-Off Delay Time	$td_{(off)}$		-	103	-	
Turn-Off Fall Time	t_f		-	44	-	
Drain-Source Diode						
Diode Forward Current	I_S	T_C=25°C (Package Limit)	-	-	340	A
Pulsed Diode Forward Current	I_{SM}		-	-	1360	
Diode Forward Voltage	V_{SD}	I_S=50A, V_{GS}=0V	-	0.8	1.3	V
Reverse Recovery Time	Trr	V_{DD}=50V,V_{GS}=0V, I_S=30A,dI_S/dt=100A/us	-	135	-	ns
Reverse Recovery Charge	Qrr		-	460	-	nC

NOTES :

1. Pulse width≤100us, Duty cycle≤2%.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an $R_{\theta JC}$=0.38°C/W.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance. Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5,-7) PCB is vertical in still air.
5. E_{AS} is calculated based on the condition of L=1mH, I_{AS}=45A, V_{DD}=50V, V_{GS}=10V. 100% test at L=0.5mH, I_{AS}=46A in production.
6. Guaranteed by design, not subject to production testing.

PJQ65702U3-AU

TYPICAL CHARACTERISTIC CURVES

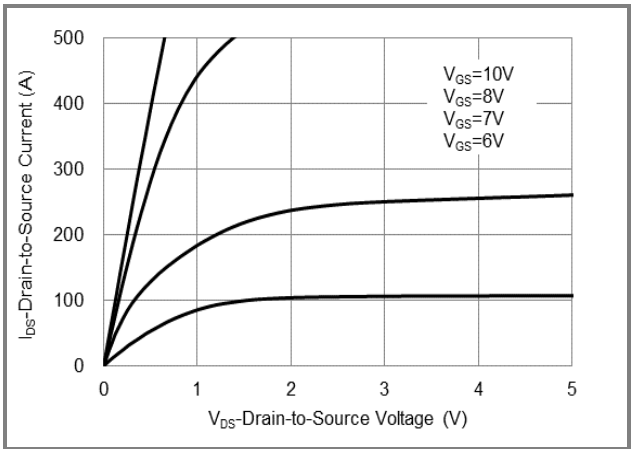


Fig.1 On-Region Characteristics

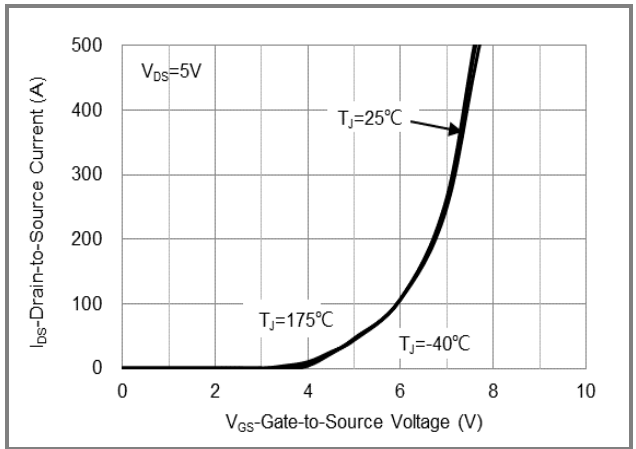


Fig.2 Transfer Characteristics

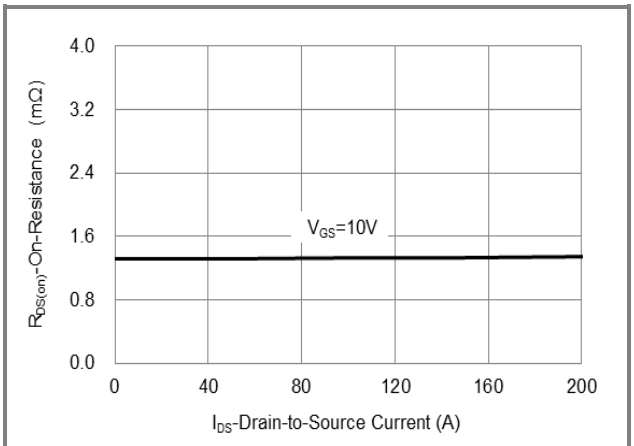


Fig.3 On-Resistance vs. Drain Current

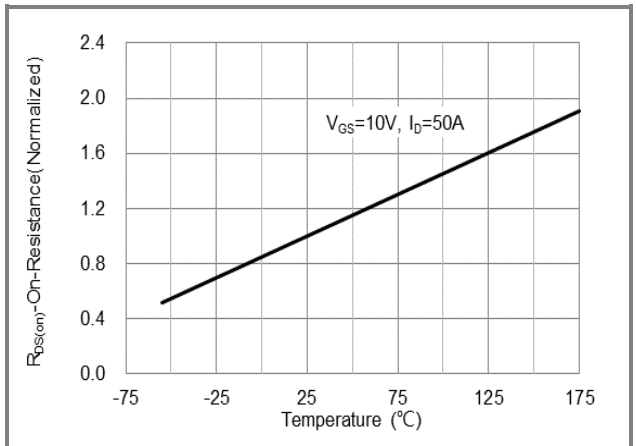


Fig.4 On-Resistance vs. Junction temperature

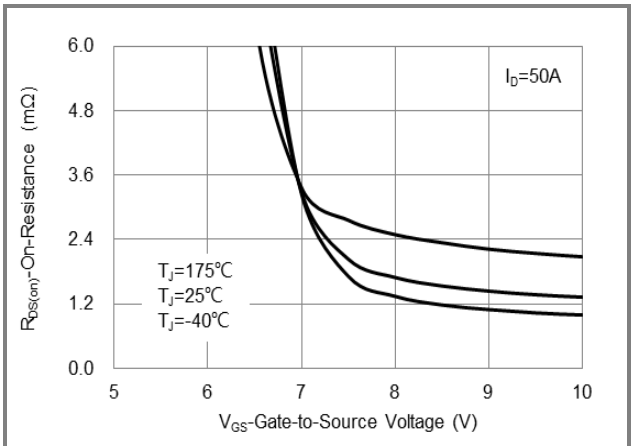


Fig.5 On-Resistance Variation with V_{GS}

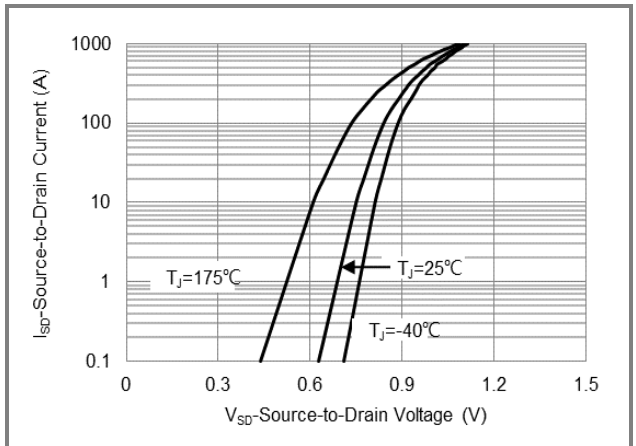


Fig.6 Source-Drain Diode Forward Voltage

PJQ65702U3-AU

TYPICAL CHARACTERISTIC CURVES

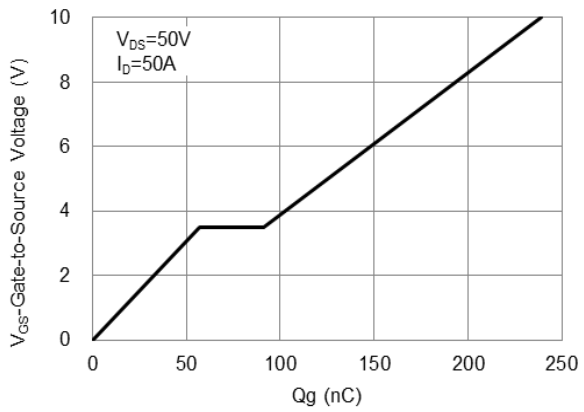


Fig.7 Gate-Charge Characteristics

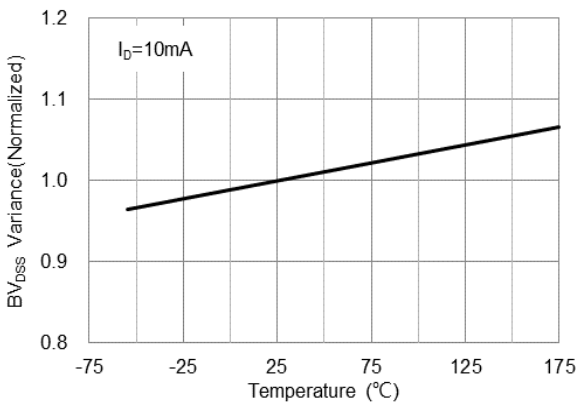


Fig.8 Breakdown Voltage Variation vs. Temperature

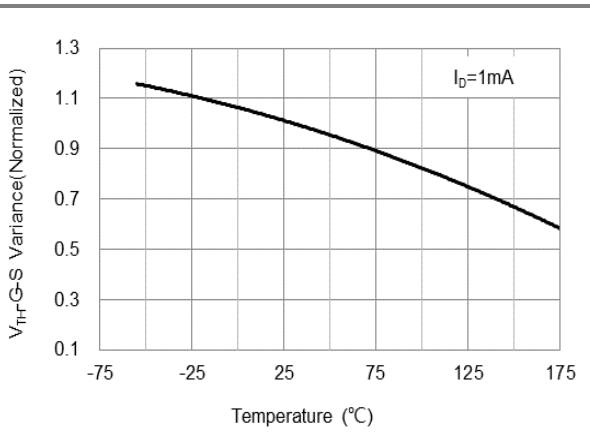


Fig.9 Threshold Voltage Variation with Temperature

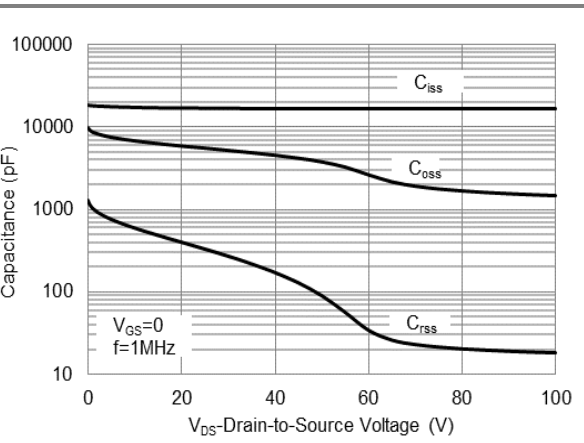


Fig.10 Capacitance vs. Drain-Source Voltage

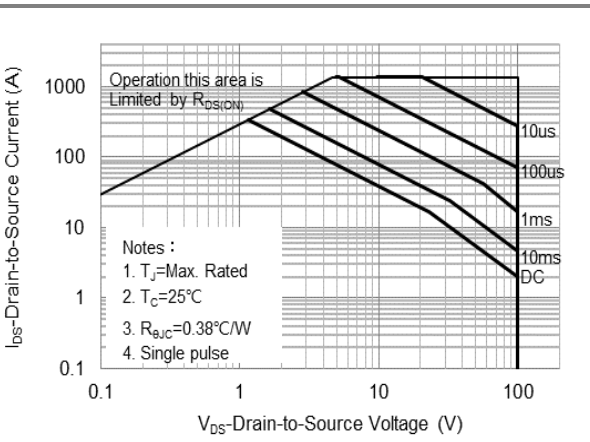


Fig.11 Maximum Safe Operating Area

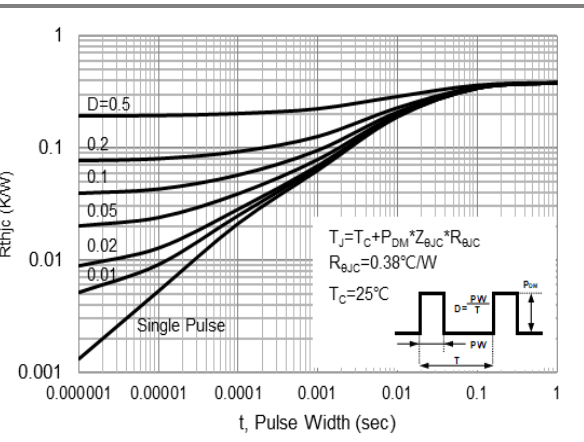


Fig.12 Normalized Transient Thermal Impedance

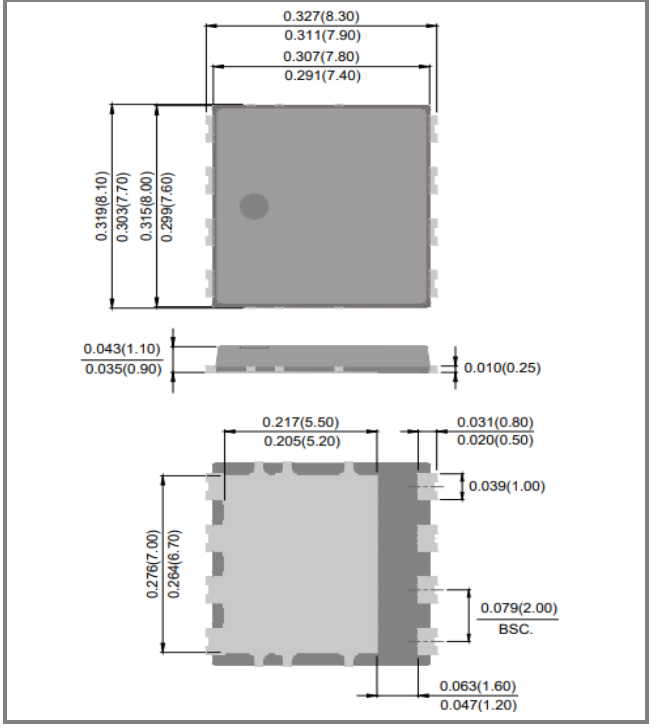
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Product and Packing Information

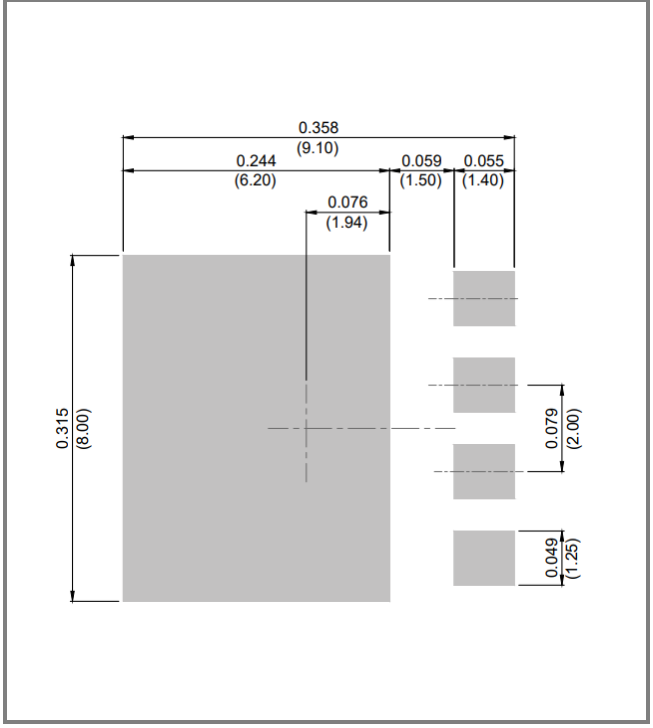
Part No.	Package Type	Packing Type	Marking
PJQ65702U3-AU	PDFN8080-8L	3K pcs / 13” reel	65702U3

Packaging Information & Mounting Pad Layout

PDFN8080-8L Dimension — Unit: inch(mm)



PDFN8080-8L Pad Layout — Unit: inch(mm)



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